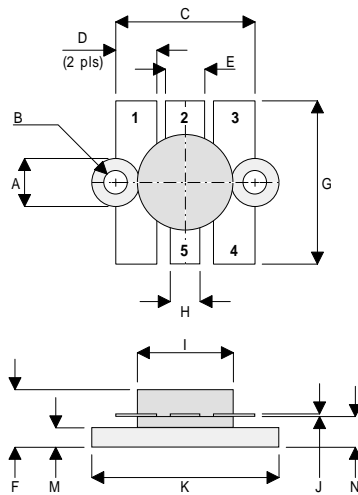


MECHANICAL DATA



DT

PIN 1 SOURCE (COMMON) PIN 2 GATE  
 PIN 3 SOURCE (COMMON) PIN 4 SOURCE (COMMON)  
 PIN 5 DRAIN

DIM	mm	Tol.	Inches	Tol.
A	6.35 DIA	0.13	0.250 DIA	0.005
B	3.17 DIA	0.13	0.125 DIA	0.005
C	18.41	0.25	0.725	0.010
D	5.46	0.13	0.215	0.005
E	5.21	0.13	0.205	0.005
F	7.62	MAX	0.300	MAX
G	21.59	0.38	0.850	0.015
H	3.94	0.13	0.155	0.005
I	12.70	0.13	0.500	0.005
J	0.13	0.03	0.005	0.001
K	24.76	0.13	0.975	0.005
M	2.59	0.13	0.102	0.005
N	4.06	0.25	0.160	0.010

**GOLD METALLISED  
 MULTI-PURPOSE SILICON  
 DMOS RF FET  
 100W – 28V – 175MHz  
 SINGLE ENDED**

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW  $C_{rss}$
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 16 dB MINIMUM

APPLICATIONS

- HF/VHF COMMUNICATIONS  
 from 1 MHz to 175 MHz

ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$P_D$	Power Dissipation	175W
$BV_{DSS}$	Drain – Source Breakdown Voltage	70V
$BV_{GSS}$	Gate – Source Breakdown Voltage	$\pm 20V$
$I_{D(sat)}$	Drain Current	25A
$T_{stg}$	Storage Temperature	$-65$ to $150^{\circ}C$
$T_j$	Maximum Operating Junction Temperature	$200^{\circ}C$

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub> Drain–Source Breakdown Voltage	V <sub>GS</sub> = 0 I <sub>D</sub> = 100mA	70			V
I <sub>DSS</sub> Zero Gate Voltage Drain Current	V <sub>DS</sub> = 28V V <sub>GS</sub> = 0			5	mA
I <sub>GSS</sub> Gate Leakage Current	V <sub>GS</sub> = 20V V <sub>DS</sub> = 0			1	μA
V <sub>GS(th)</sub> Gate Threshold Voltage *	I <sub>D</sub> = 10mA V <sub>DS</sub> = V <sub>GS</sub>	1		7	V
g <sub>fs</sub> Forward Transconductance *	V <sub>DS</sub> = 10V I <sub>D</sub> = 4A	4			S
G <sub>PS</sub> Common Source Power Gain	P <sub>O</sub> = 100W	16			dB
η Drain Efficiency	V <sub>DS</sub> = 28V I <sub>DQ</sub> = 0.5A	50			%
VSWR Load Mismatch Tolerance	f = 175MHz	20:1			—
C <sub>iss</sub> Input Capacitance	V <sub>DS</sub> = 28V V <sub>GS</sub> = -5V f = 1MHz			300	pF
C <sub>oss</sub> Output Capacitance	V <sub>DS</sub> = 28V V <sub>GS</sub> = 0 f = 1MHz			150	pF
C <sub>rss</sub> Reverse Transfer Capacitance	V <sub>DS</sub> = 28V V <sub>GS</sub> = 0 f = 1MHz			12.5	pF

\* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

## HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

**THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.**

## THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max. 1.0°C / W
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